

Measurement of Hydroxyl Radicals in Wafer Cleaning Solutions Irradiated with Megasonic Field

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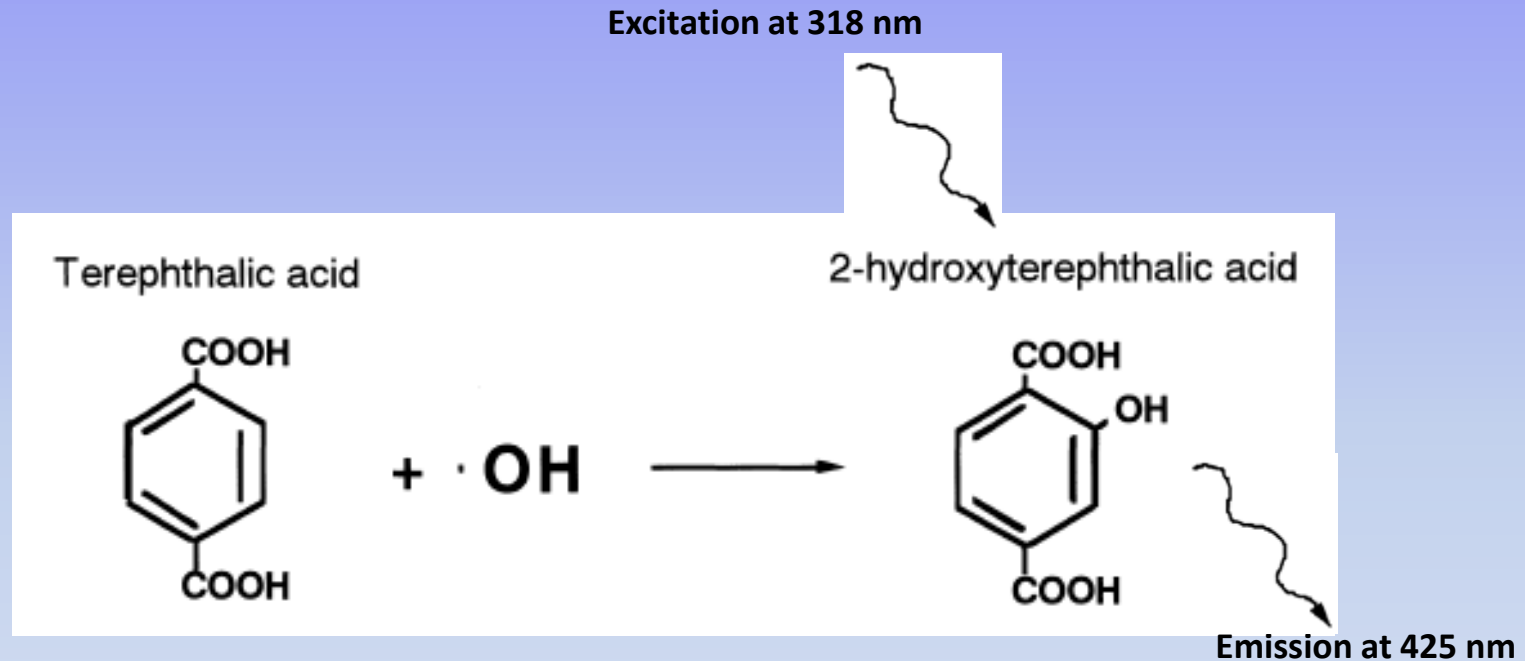
Introduction

- ❖ **Megasonic irradiation of liquids is known to generate free radicals**
- ❖ **Traditionally, formation of hydroxyl radical (OH^\bullet) in acoustically irradiated solutions has been qualitatively identified using sonoluminescence spectrum**
- ❖ **Limited studies on measurement of OH^\bullet concentration have focused on aqueous solutions of near neutral pH with megasonic ($\sim 1\text{-}3$ MHz) exposure using a sonic probe**
- ❖ **Since OH^\bullet have strong oxidizing potential, systematic Investigations of hydroxyl radical generation in wafer cleaning solutions using immersion and single wafer meg systems would be of interest to semiconductor industry**

Key Objective and Approach

- **Key Objective :**
 - Measure concentration of hydroxyl radicals generated in megasonic irradiated solutions under immersion and single wafer cleaning conditions
- **Approach:**
 - Fluorometric technique based on complexation of OH radicals by terephthalic acid
 - Key experimental variables investigated: solution pH, temperature, type and concentration of dissolved gases, transducer power density and exposure time

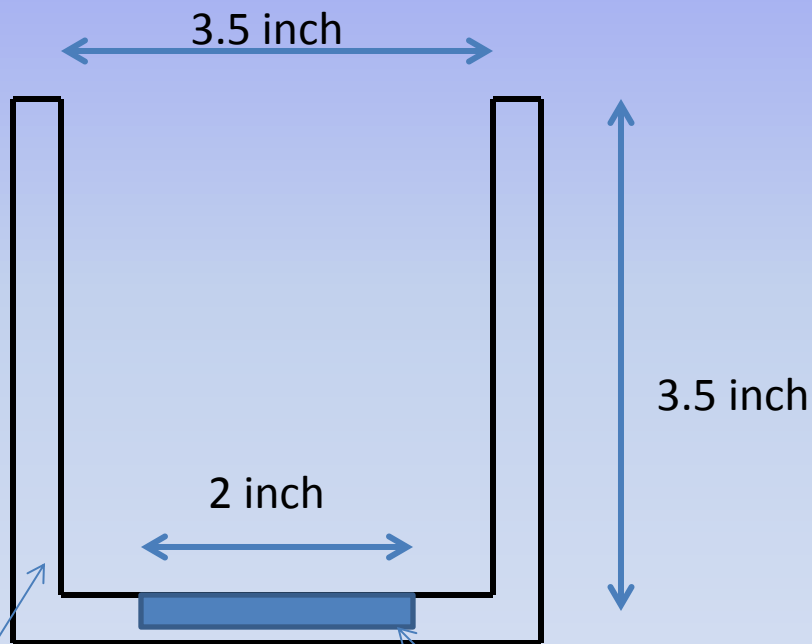
Fluorescence Spectroscopy Using Terephthalic Acid



- Hydroxyl radical trapped using terephthalic acid to form 2-hydroxyterephthalic acid, measured using fluorescence spectroscopy
- 2-hydroxyterephthalic acid is stable up to 6 hours at room temperature

Megasonic Systems (ProSys) Used for Experimental Investigations

**Megbowl® – Immersion type (~ 1 MHz freq.
0.1-2.0 W/cm² power density)**

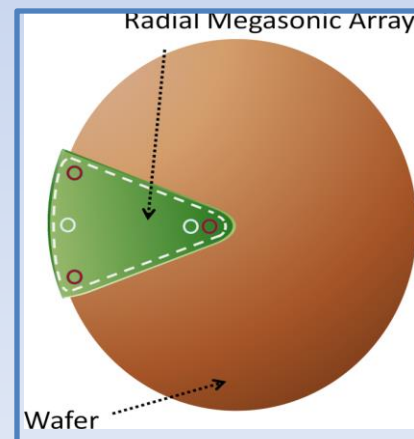
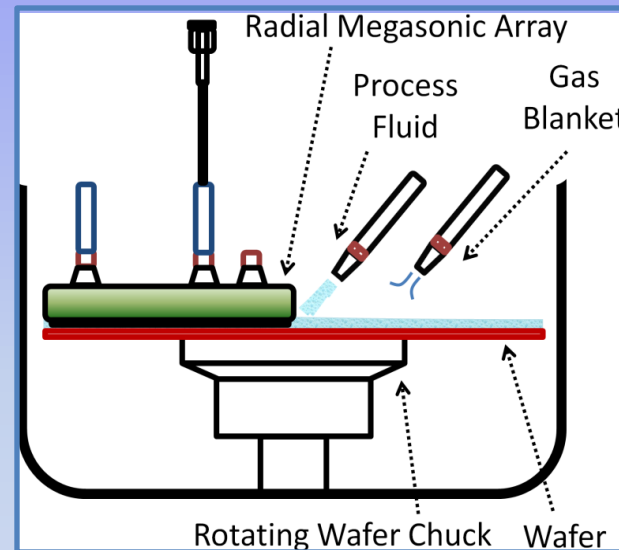


polypropylene

circular transducer with
sapphire resonator
on top

Megbowl® and MegPie® are registered
trademarks of ProSys (Campbell, CA)

**MegPie® – Single wafer (~ 1 MHz freq.
0.1-3.0 W/cm² power density)**

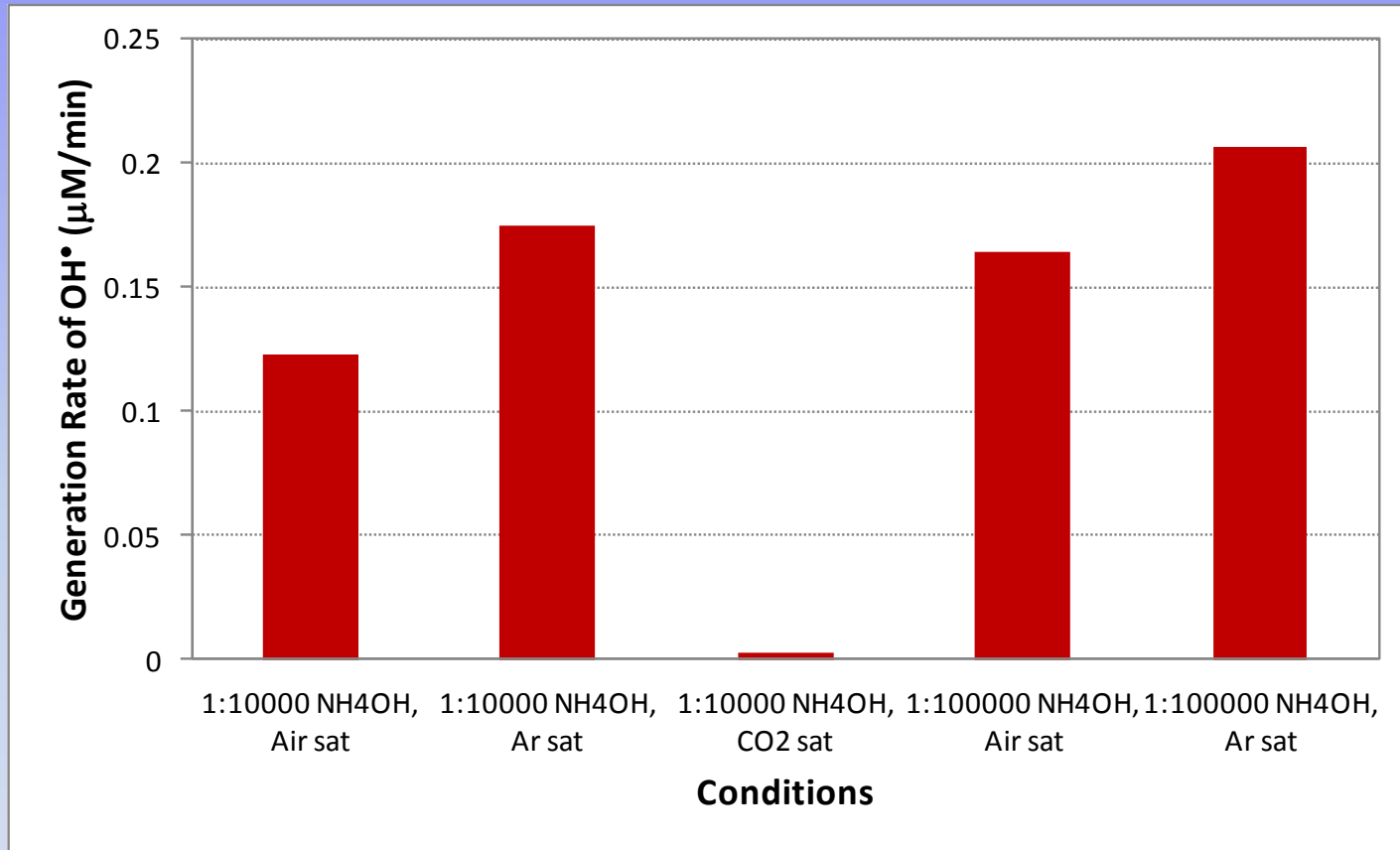


Experimental Procedures

- Chemical/gas of interest (Ar, CO₂, NH₄OH, TMAH, KOH, or phosphate buffer) was bubbled/added to achieve desired composition and pH. Solution heated/cooled to a different temperature if desired. Solution was air saturated unless stated otherwise
- All solutions contained ~ 75 μM of Terephthalic acid
- Solutions subjected to ~ 1 MHz sound field at 0.1 to 2 W/cm² (**ProSys Megbowl**[®] or **MegPie**[®]) for different times at 25 deg C (unless stated otherwise).
- Fluorescence intensity measured at 425 nm (excitation at 318 nm) using RF-5301PC Spectrofluorometer
- For calibration, solutions containing hydroxy terephthalic acid instead of terephthalic acid were used

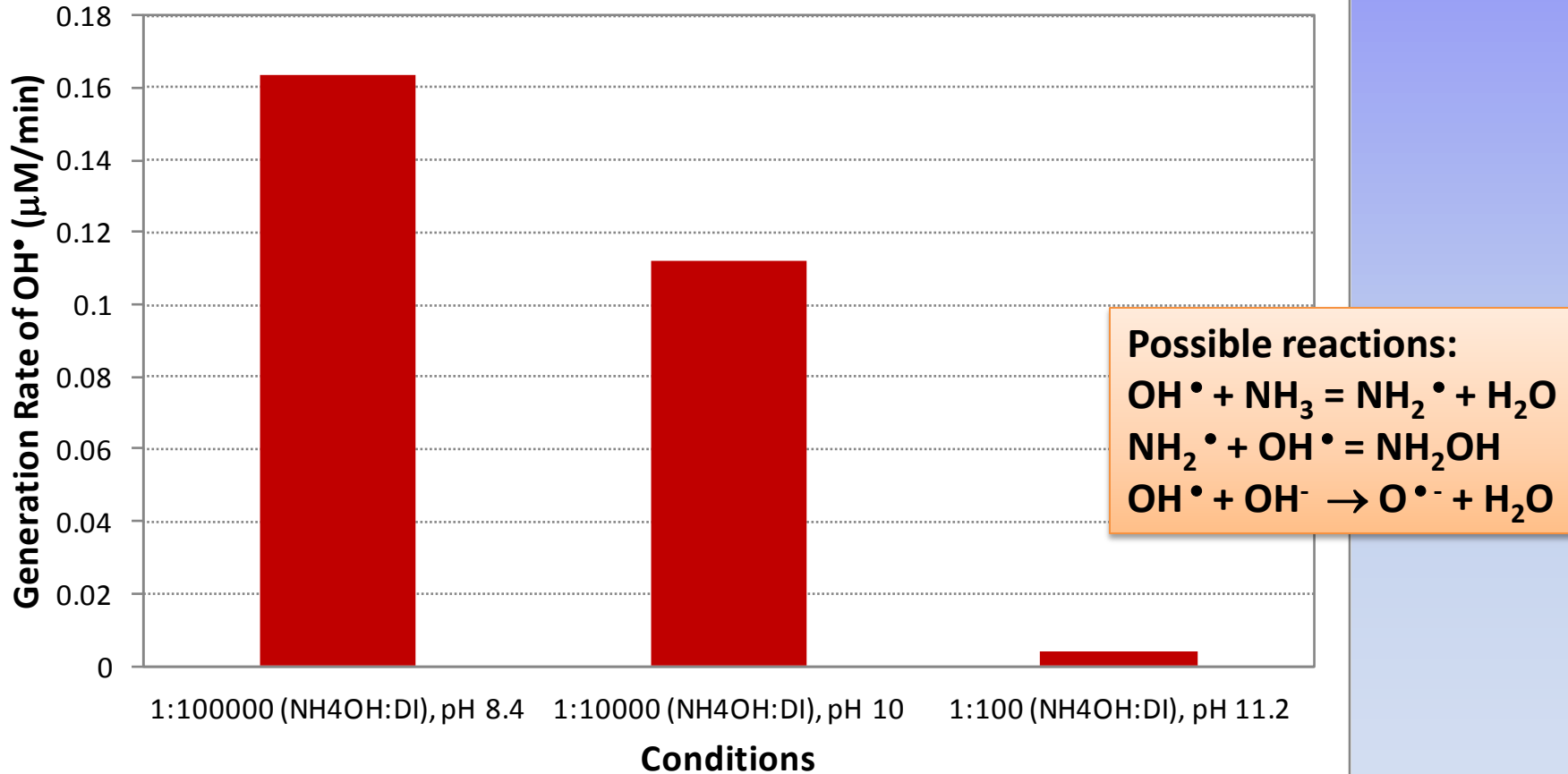
Phase I- Experimental Investigations in **Immersion Meg System**

Effect of Dissolved Gases on Hydroxyl Radical Generation in NH_4OH solutions at 2 W/cm^2



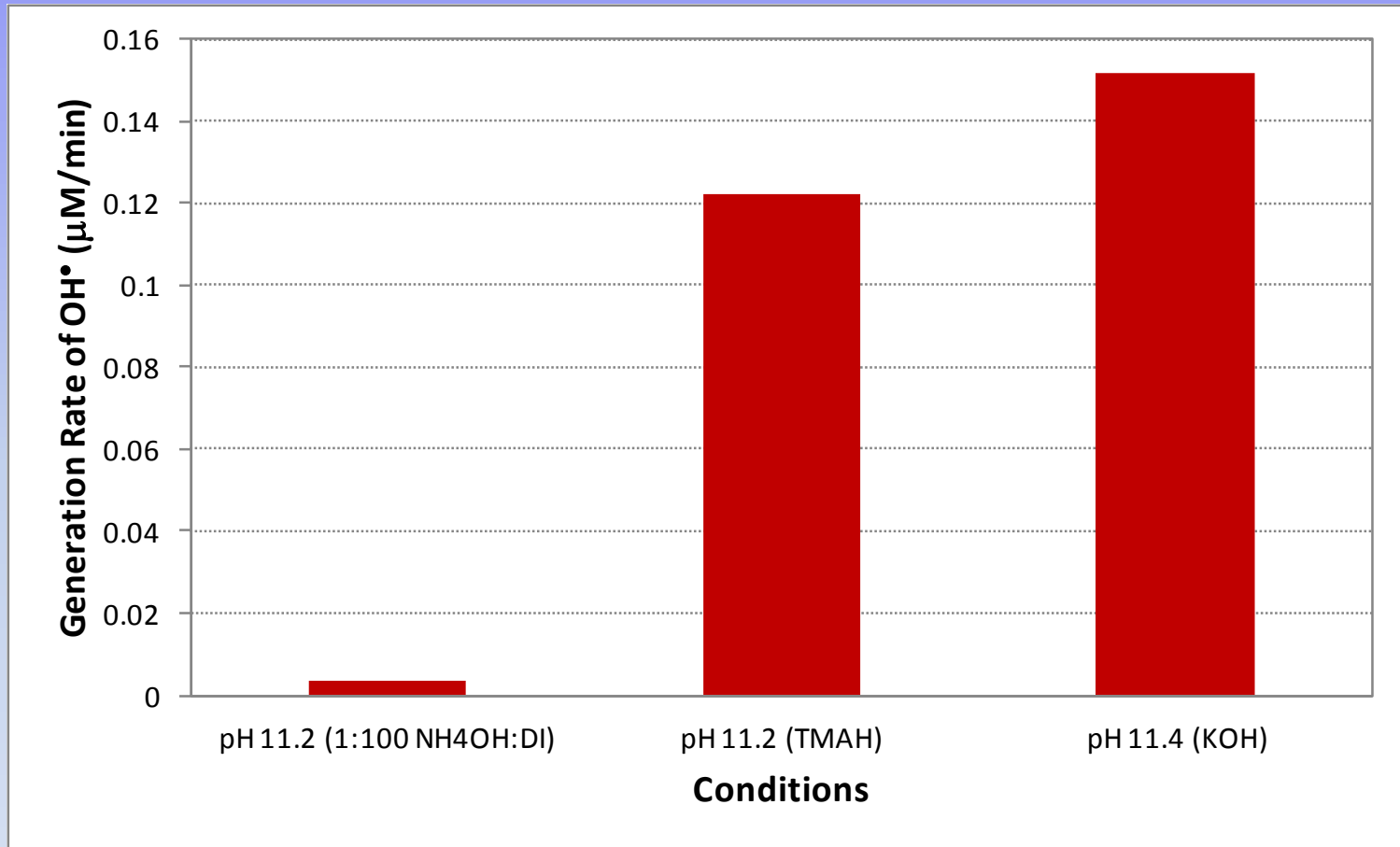
- Hydroxyl radical generation higher in Ar saturated solutions compared to air saturated solutions
- No measurable OH^\bullet conc. in CO_2 saturated solutions

Effect of Ammonia on Hydroxyl Radical Production at Megasonic Power Density of 2 W/cm²



Generation rate of OH[•] decreases with increase in NH₄OH concentration

Effect of pH on Hydroxyl Radical Production at Megasonic Power Density of 2 W/cm²

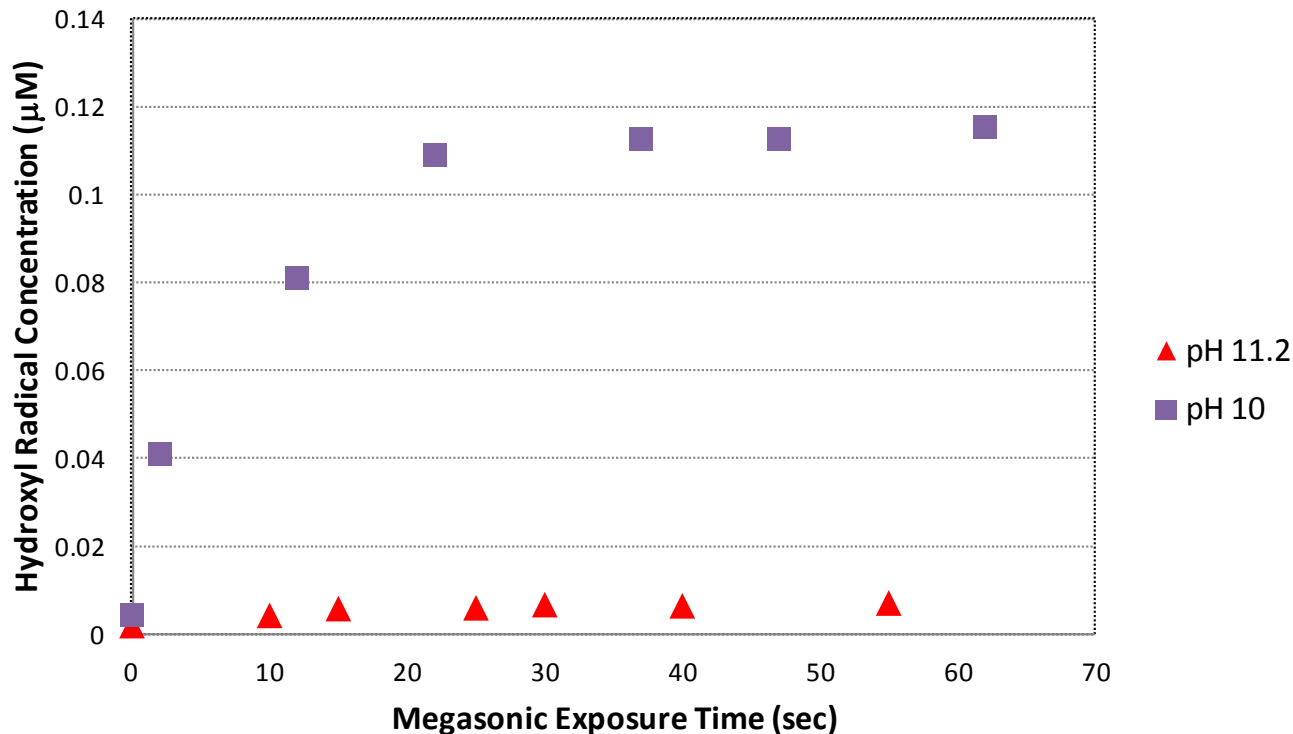


At pH ~11.2, generation rate of OH• depends on type of alkali used

Phase II- Experimental Investigations in **Single wafer Meg System**

Effect of Ammonia on Hydroxyl Radical Production at Megasonic Power Density of 2 W/cm²

- Dispense ammoniacal solutions containing terephthalic acid at 300 ml/min on 8" Si wafer rotating at 30 rpm
- Start meg exposure after 5 s, collect samples from effluent streams and analyze for OH[•]



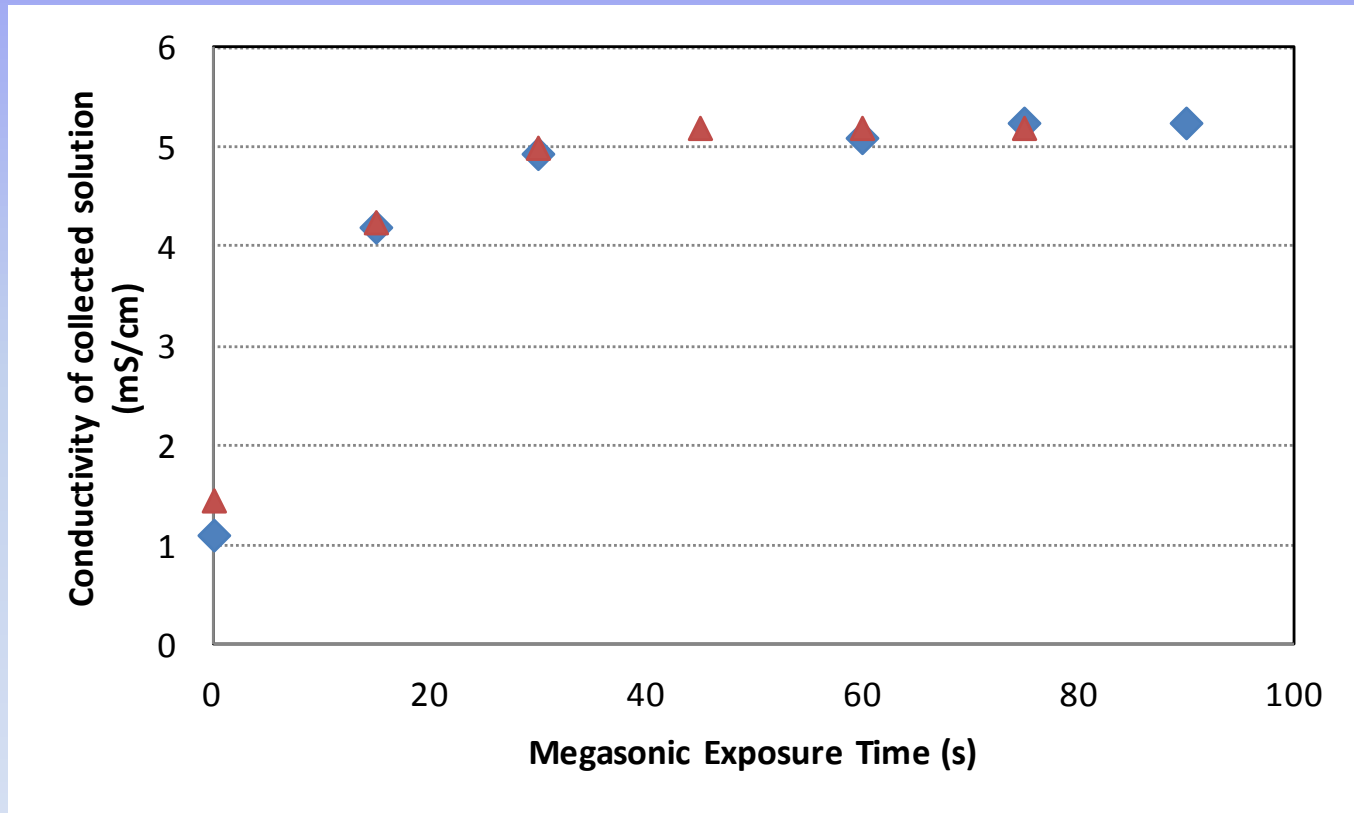
Concentration of OH[•] increases with meg exposure time

Residence time effect?

- Hydroxyl radical concentration decreases with increase in NH₄OH conc.
- Concentration of OH[•] similar to that generated in immersion meg system

Investigation of Residence Time using an Electrolyte (KCl)

- Dispense water (conductivity $\sim 1 \mu\text{S}/\text{cm}$) at 300 ml/min on 8" Si wafer rotating at 30 rpm
- Replace water by KCl solution of conductivity $\sim 5.3 \text{ mS}/\text{cm}$ and start meg
- Collect samples from effluent stream and analyze for conductivity



- **Almost similar time ($\sim 30 \text{ s}$) for KCl to replace DI water as the time for reaching constant OH^\bullet conc. during meg exposure (previous slide)**

Summary

- Generation rate of OH^\bullet ↓ with NH_4OH concentration
- In aqueous NH_4OH solutions saturated with various dissolved gases, generation rate of OH^\bullet decreases in the following order:
 $\text{Ar} > \text{Air} > \text{CO}_2$
- At pH ~11.2, generation rate of OH^\bullet depends on type of alkali used
- Generation of OH^\bullet concentration was very similar in immersion and single wafer megasonic systems suggesting that single wafer meg tool is as effective as immersion meg tool